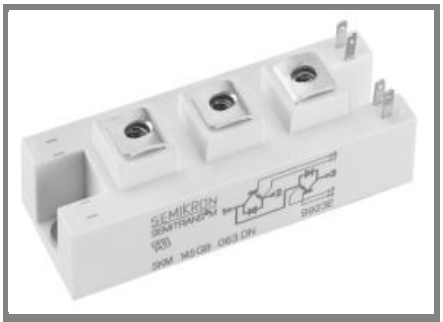
SKM 100GB125DN



SEMITRANS^{TM} 2N

Ultra Fast IGBT Module

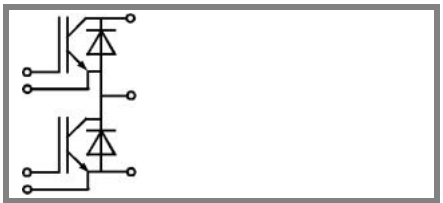
SKM 100GB125DN

Features

- N channel, homogeneous Si
- Low inductance case
- Short tail current with low temperature dependence
- High short circuit capability, self limiting to 6 x I_{cnom}
- Fast & soft inverse CAL diodes
- Isolated copper baseplate using DCB Direct Copper Bonding Technology
- Large clearance (10 mm) and creepage distances (20 mm)

Typical Applications

- Switched mode power supplies at f_{sw} > 20 kHz
- Resonant inverters up to 100 kHz
- Inductive heating
- Electronic welders at f_{sw} > 20 kHz



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Absolute Maximum Ratings		T_c = 25 °C, unless otherwise specified	
Symbol	**Conditions**	**Values**	**Units**
IGBT			
V_{CES}		1200	V
I_C	T_c = 25 (85) °C	100 (80)	A
I_{CRM}	t_p = 1 ms	150	A
V_{GES}		± 20	V
T_{vj}, (T_{stg})	$T_{OPERATION} \leq T_{stg}$	- 40 ... + 150 (125)	°C
V_{isol}	AC, 1 min.	4000	V
Inverse diode			
I_F	T_c = 25 (80) °C	95 (65)	A
I_{FRM}	t_p = 1 ms	150	A
I_{FSM}	t_p = 10 ms; sin.; T_j = 150 °C	720	A

Characteristics		T_c = 25 °C, unless otherwise specified			
Symbol	**Conditions**	**min.**	**typ.**	**max.**	**Units**
IGBT					
$V_{GE(th)}$	V_{GE} = V_{CE}, I_C = 2 mA	4,5	5,5	6,5	V
I_{CES}	V_{GE} = 0, V_{CE} = V_{CES}, T_j = 25 (125) °C		0,15	0,45	mA
$V_{CE(TO)}$	T_j = 25 (125) °C				V
r_{CE}	V_{GE} = 15 V, T_j = 25 (125) °C				mΩ
$V_{CE(sat)}$	I_{Cnom} = 75 A, V_{GE} = 15 V, chip level		3,3	3,85	V
C_{ies}	under following conditions		5	6,6	nF
C_{oes}	V_{GE} = 0, V_{CE} = 25 V, f = 1 MHz		0,72	0,9	nF
C_{res}			0,38	0,5	nF
L_{CE}				25	nH
$R_{CC'+EE'}$	res., terminal-chip T_c= °C				mΩ
$t_{d(on)}$	V_{CC} = 600 V, I_{Cnom} = 75 A		80		ns
t_r	R_{Gon} = R_{Goff} = 8 Ω, T_j = 125 °C		40		ns
$t_{d(off)}$	V_{GE} = ± 15 V		360		ns
t_f			20		ns
E_{on} (E_{off})			9 (3,5)		mJ
Inverse diode					
V_F = V_{EC}	I_{Fnom} = 75 A; V_{GE} = 0 V; T_j = 25 (125) °C		2 (1,8)	2,5	V
$V_{(TO)}$	T_j = 25 (125) °C		1,1	1,2	V
r_T	T_j = 25 (125) °C		12	17,3	mΩ
I_{RRM}	I_{Fnom} = 75 A; T_j = 125 ( ) °C		50		A
Q_{rr}	di/dt = 800 A/µs		11,5		µC
E_{rr}	V_{GE} = 0 V		4		mJ
Thermal characteristics					
$R_{th(j-c)}$	per IGBT			0,18	K/W
$R_{th(j-c)D}$	per Inverse Diode			0,5	K/W
$R_{th(c-s)}$	per module			0,05	K/W
Mechanical data					
M_s	to heatsink M6	3		5	Nm
M_t	to terminals M5	2,5		5	Nm
w				160	g

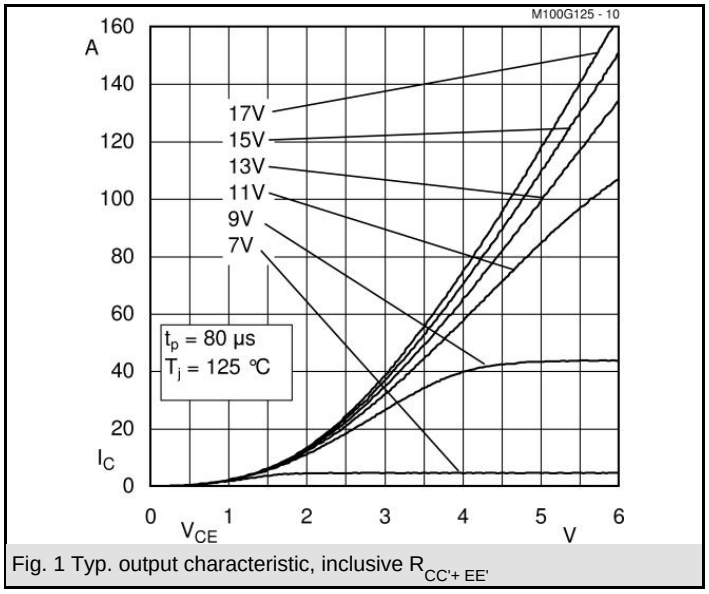


Fig. 1 Typ. output characteristic, inclusive $R_{CC'+EE'}$

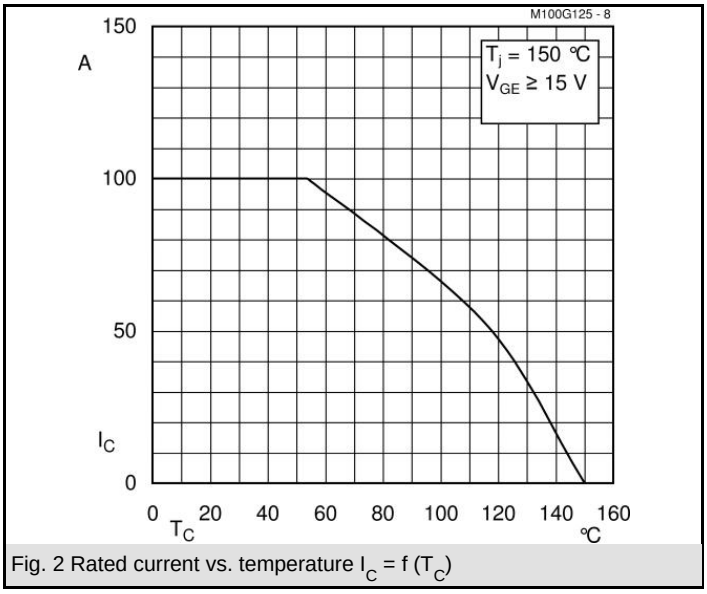


Fig. 2 Rated current vs. temperature $I_C = f(T_C)$

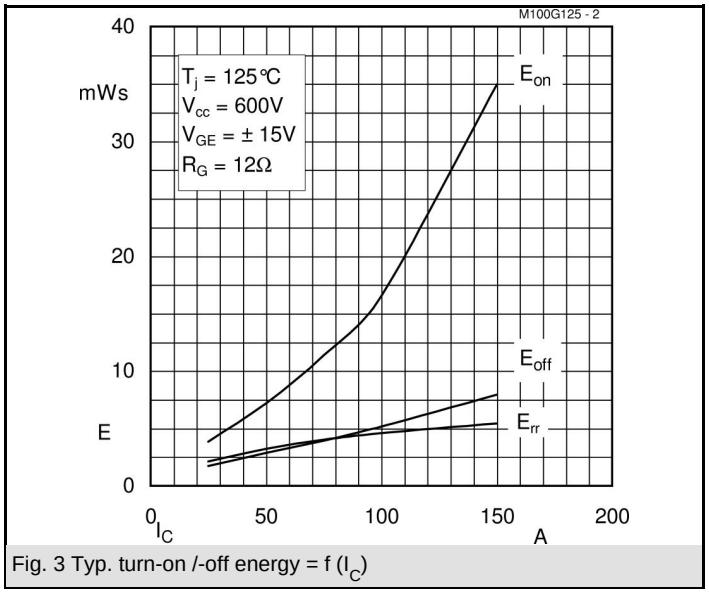


Fig. 3 Typ. turn-on /-off energy = f (I_C)

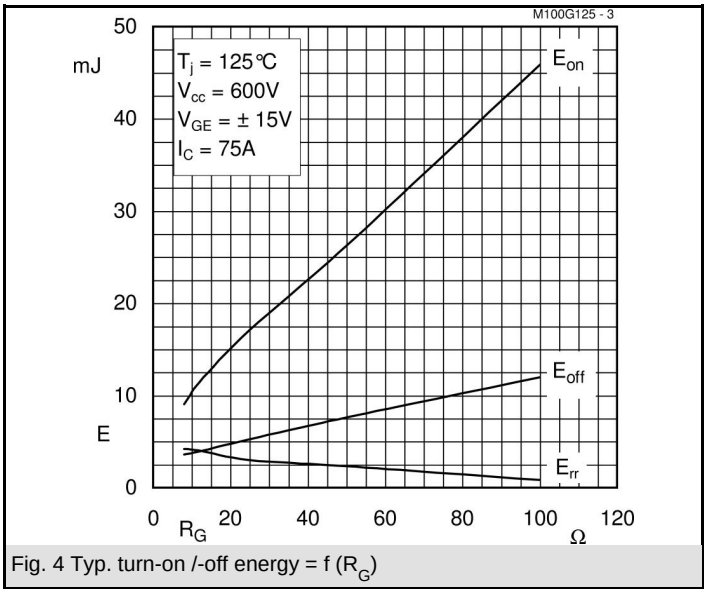


Fig. 4 Typ. turn-on /-off energy = f (R_G)

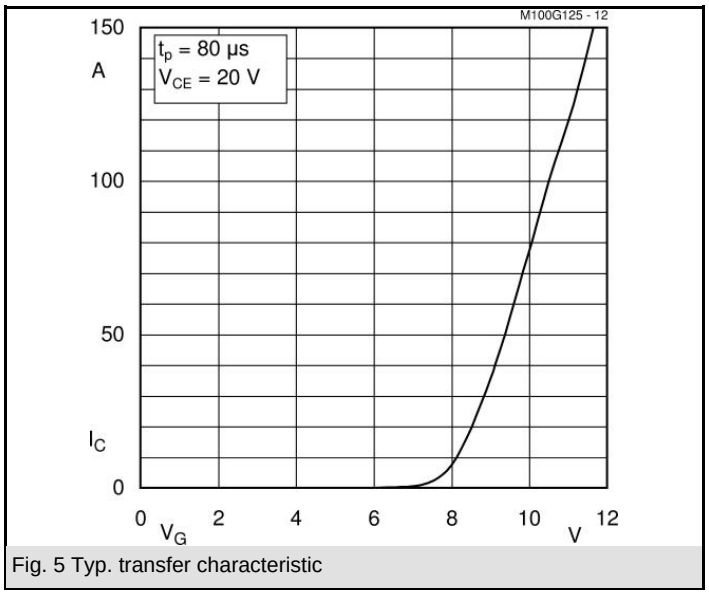


Fig. 5 Typ. transfer characteristic

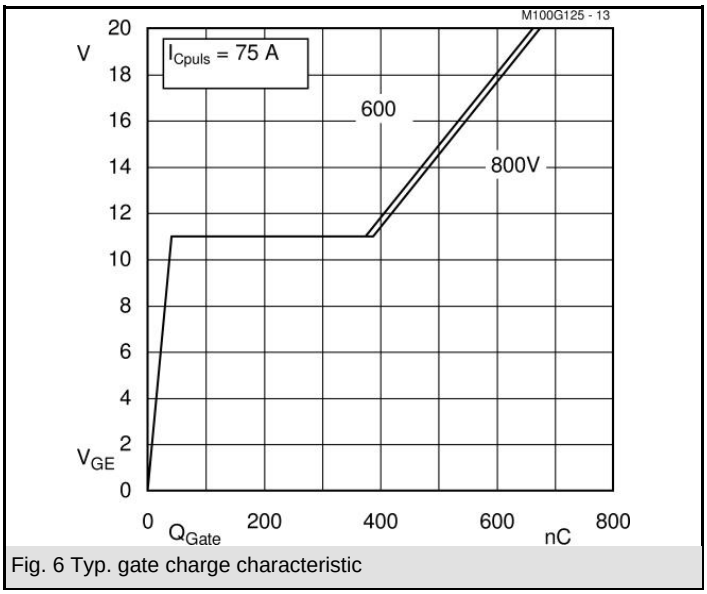


Fig. 6 Typ. gate charge characteristic

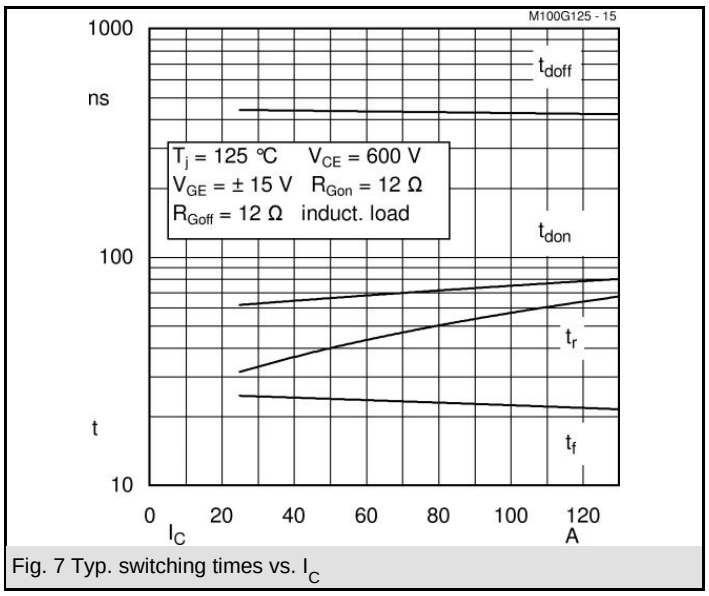


Fig. 7 Typ. switching times vs. I_C

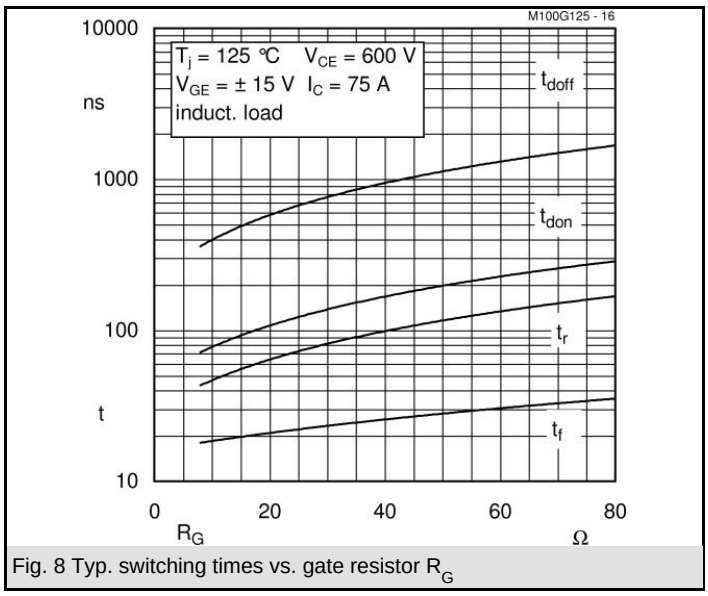


Fig. 8 Typ. switching times vs. gate resistor R_G

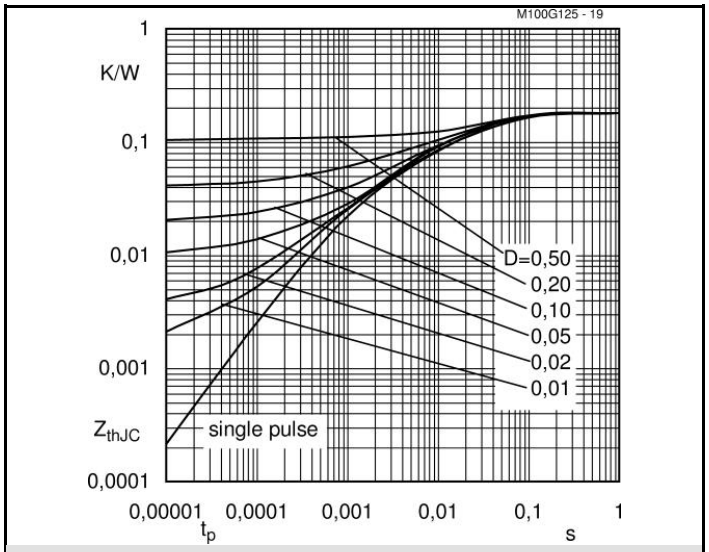


Fig. 9 Transient thermal impedance of IGBT

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

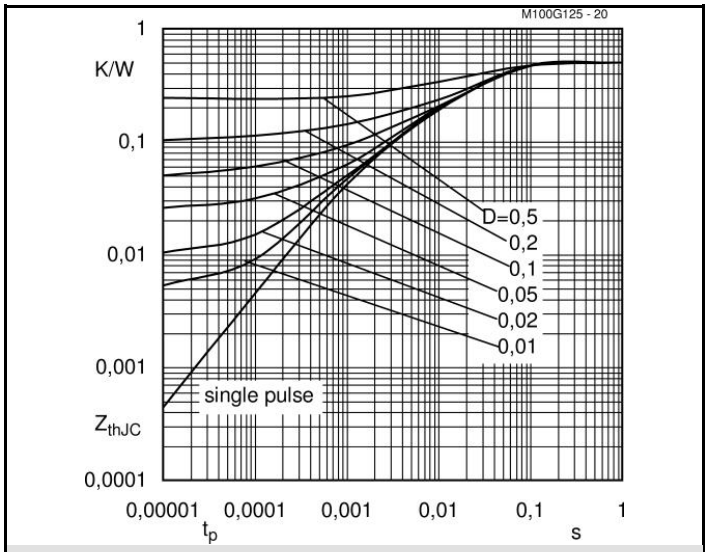


Fig. 10 Transient thermal impedance of FWD

$Z_{thp(j-c)} = f(t_p)$; $D = t_p/t_c = t_p * f$

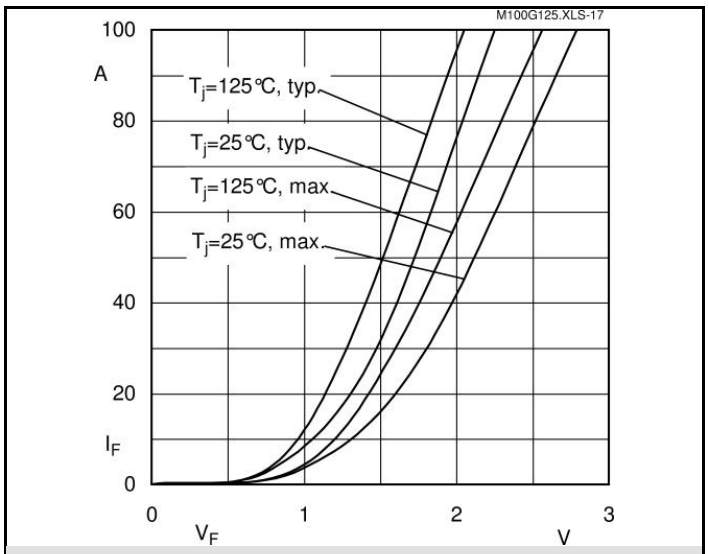


Fig. 11 CAL diode forward characteristic

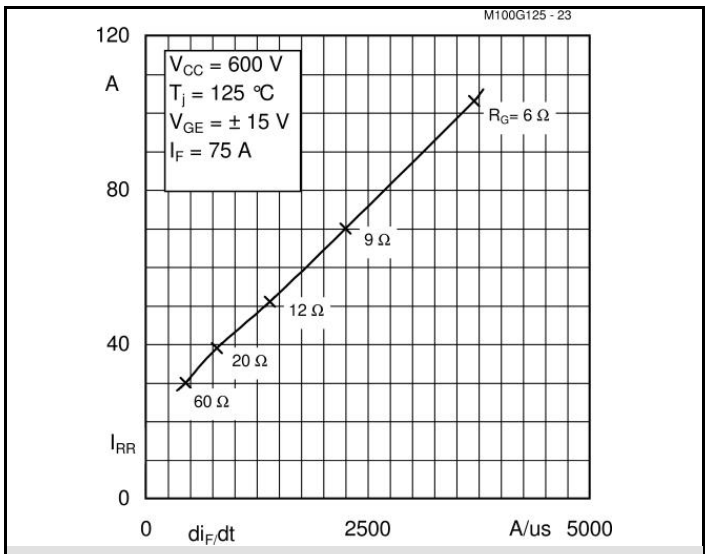


Fig. 12 Typ. CAL diode peak reverse recovery current

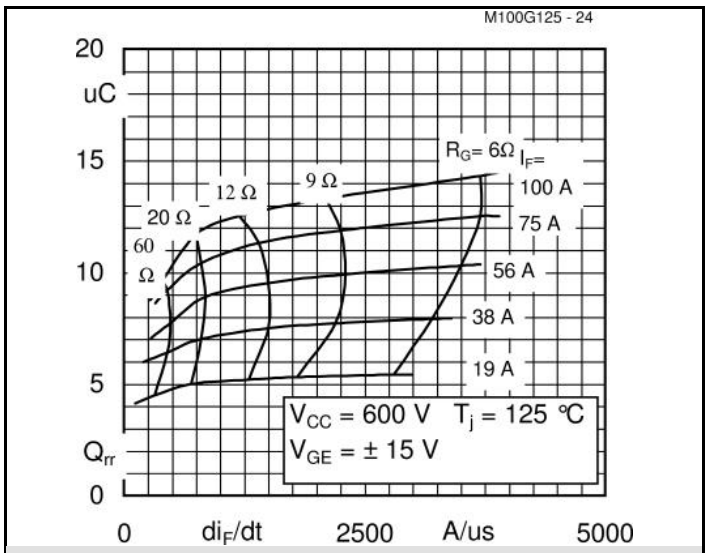
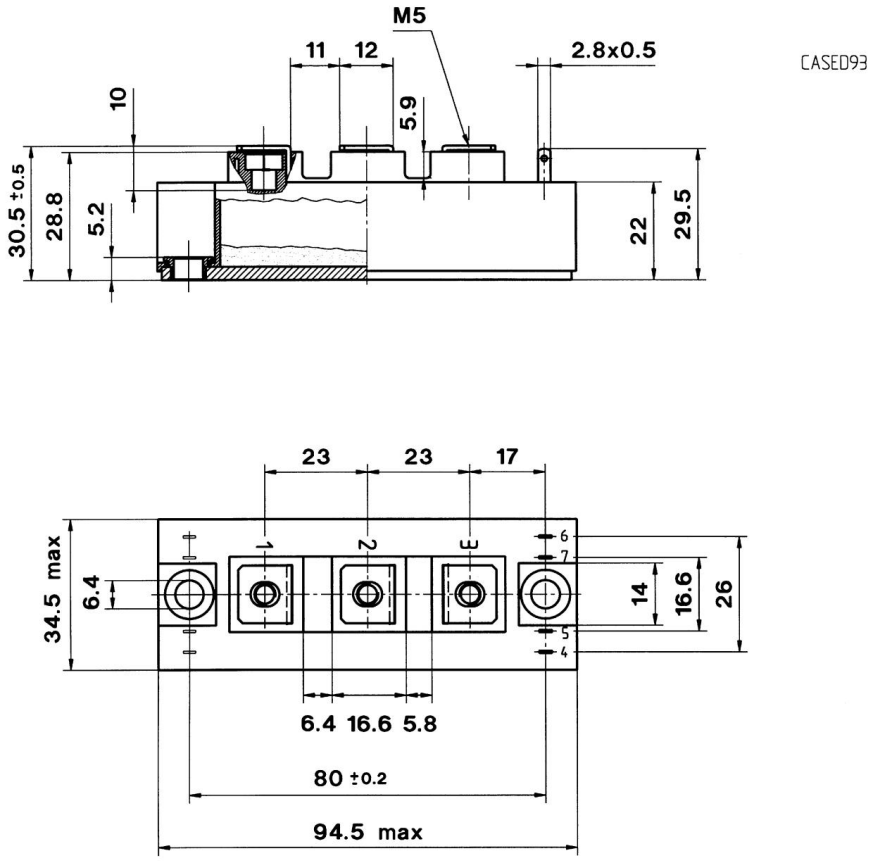


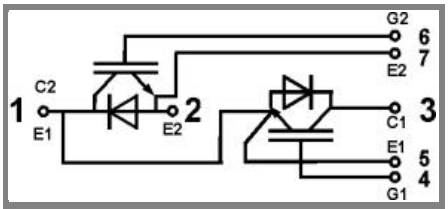
Fig. 13 Typ. CAL diode recovered charge

UL Recognized
File no. E 63 532

Dimensions in mm



Case D 93



GB Case D 93

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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